

2N6394





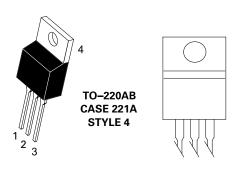
Description

Designed primarily for half-wave ac control applications, such as motor controls, heating controls and power supplies.

Features

- Glass Passivated
 Junctions for Greater
 Parameter Uniformity and
 Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in all Four Quadrants
- For 400 Hz Operation, Consult Factory
- 8.0 A Devices Available as 2N6344 thru 2N6349
- Pb-Free Package is Available

Pin Out



Functional Diagram



Additional Information









Samples

Maximum Ratings † (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit	
Peak Repetitive Off-State Voltage (Note 1) $(T_J = -40 \text{ to } 110^{\circ}\text{C}, \text{ Sine Wave, } 50 \text{ to } 60 \text{ Hz, Gate Open)}$	2N6394 2N6395 2N6397 2N6399	V _{drm} , V _{rrm}	50 100 400 800	V
On-State RMS Current (180° Conduction Angles; $T_c = 90$ °C)		I _{T (RMS)}	12	А
Peak Non–Repetitive Surge Current (1/2 Cycle, Sine Wave, 60 Hz, T _J = 90°C)		I _{TSM}	100	А
Circuit Fusing Considerations (t = 8.3 ms)		l _{2t}	40	A ² s
Forward Peak Gate Power (Pulse Width $\leq 1.0 \mu s$, $T_c = 90^{\circ}C$)		P _{GM}	20	W
Forward Average Gate Power (t = 8.3 ms , $T_c = 90^{\circ}\text{C}$)		P _{G(AV)}	0.5	W
Forward Peak Gate Current (Pulse Width ≤ 1.0 µs, T _C = 90°C)		I _{GM}	2.0	А
Operating Junction Temperature Range		T _J	-40 to +125	°C
Storage Temperature Range		T _{stg}	-40 to +125	°C

†Indicates JEDEC Registered Data

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Thermal Characteristics

Rating	Symbol	Value	Unit
† Thermal Resistance, Junction to Case	R _{sJC}	2.0	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	T _L	260	°C

[†] Indicates JEDEC Registered Data.

Electrical Characteristics - OFF (T_c = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic	Symbol	Min	Тур	Max	Unit
*Peak Repetitive Blocking Current T = 25'	: I _{DRM} ,	-	-	1.0	μΑ
$(V_D = V_{DRM} = V_{RRM}; Gate Open)$ $T_J = 100$		-	-	2.0	mA

Electrical Characteristics - **ON** ($T_c = 25$ °C unless otherwise noted; Electricals apply in both directions)

Characteristic	Symbol	Min	Тур	Max	Unit
†Peak Forward On–State Voltage (Note 2) (I _{TM} = 24 A Peak)	V _{TM}	_	1.7	2.2	V
†Gate Trigger Voltage (Continuous DC), All Quadrants (Continuous dc) (V _D = 12 Vdc, R _L = 100 Ohms)		_	5.0	30	mA
†Gate Trigger Voltage (Continuous dc) (V _D = 12 Vdc, R _L = 100 Ohms)		-	0.7	1.5	V
Gate Non–Trigger Voltage ($V_D = 12 \text{ Vdc}$, $R_L = 100 \text{ Ohms}$, $T_J = 125 ^{\circ}\text{C}$)		0.2	_	_	V
†Holding Current (V _D = 12 Vdc, Initiating Current = 200 mA, Gate Open)		-	6.0	50	mA
Turn-On Time ($I_{TM} = 12 \text{ A}, I_{GT} = 40 \text{ mAdc}, V_D = \text{Rated } V_{DRM}$)		_	1.0	2.0	μs
The Off Time (V) Potential (I _{TM} = 12 A, I _R = 12 A)	_	-	-	15	
Turn-Off Time (V_D = Rated V_{DRM}) $(I_{TM} = 12 \text{ A}, I_R = 12 \text{ A}, T_J = 125 ^{\circ}\text{C})$	L _q	-	-	35	μs

†Indicates JEDEC Registered Data

V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

^{2.} Pulse Test: Pulse Width \leq 300 µsec, Duty Cycle \leq 2%.



Dynamic Characteristics

Characteristic	Symbol	Min	Тур	Max	Unit
Critical Rate-of-Rise of Off-State Voltage Expovnential ($V_D = Rated V_{DRM'} T_J = 125$ °C)	dv/dt(c)	-	50	_	V/µs

Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
V _{DRM}	Peak Repetitive Forward Off State Voltage
I _{DRM}	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Reverse Off State Voltage
I _{RRM}	Peak Reverse Blocking Current
V _{TM}	Maximum On State Voltage
I _H	Holding Current

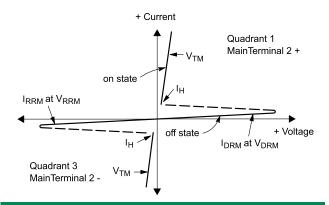


Figure 1. Current Derating

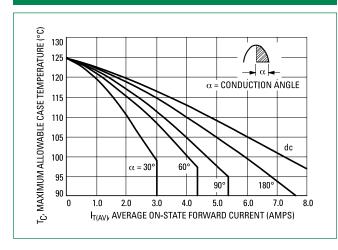


Figure 2. Maximum On-State Characteristics

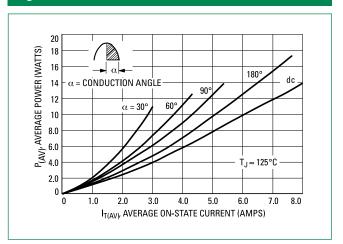




Figure 3. On-State Characteristics

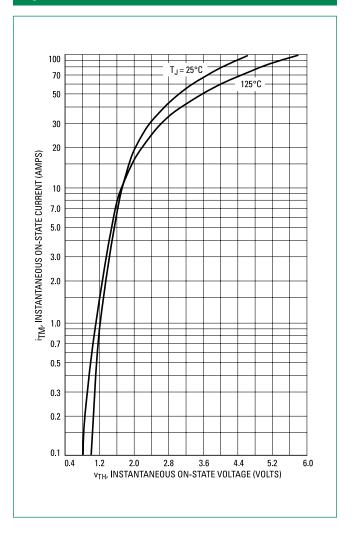


Figure 4. Maximum Non-Repetitive Surge Current

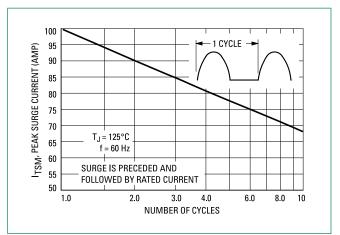
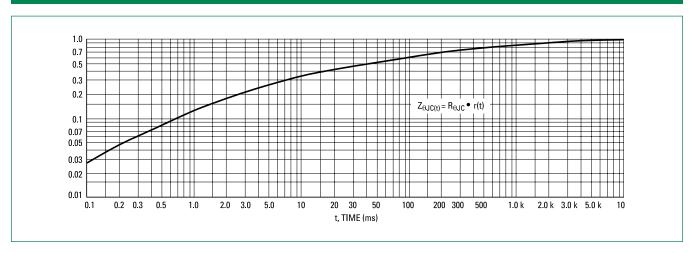


Figure 5. Typical Thermal Response





Typical Characteristics

Figure 6. Typical Gate Trigger Current vs. Pulse Width

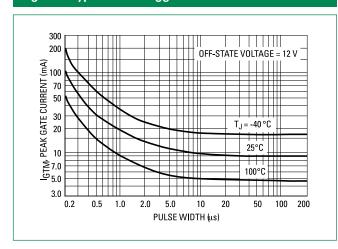


Figure 7. Typical Gate Trigger Current vs. Temperature

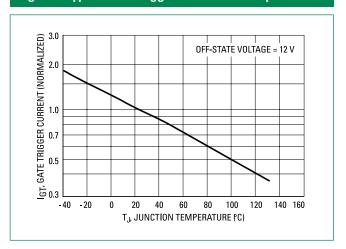


Figure 8. Typical Gate Trigger Voltage vs. Temperature

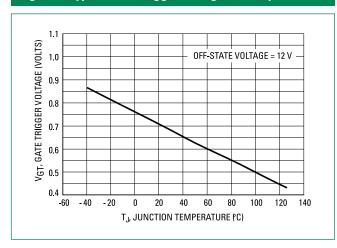
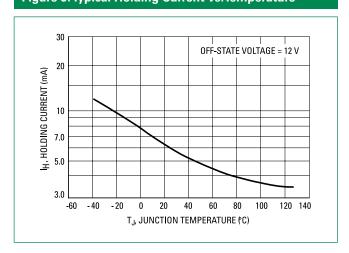
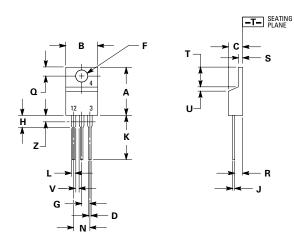


Figure 9. Typical Holding Current vs. Temperature

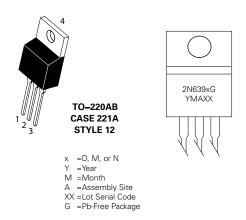




Dimensions



Part Marking System



D:	Inches		Millin	neters
Dim	Min	Max	Min	Max
Α	0.590	0.620	14.99	15.75
В	0.380	0.420	9.65	10.67
С	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.41	2.67
Н	0.110	0.130	2.79	3.30
J	0.018	0.024	0.46	0.61
K	0.540	0.575	13.72	14.61
L	0.060	0.075	1.52	1.91
N	0.195	0.205	4.95	5.21
Q	0.105	0.115	2.67	2.92
R	0.085	0.095	2.16	2.41
S	0.045	0.060	1.14	1.52
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Z		0.080		2.04

Pin Assignment			
1	Cathode		
2	Anode		
3	Gate		
4	Anode		

Ordering	Information
Ordering	minomination

Device	Package	Shipping
2N6394G		500 Units / Box
2N6394TG		500 Units / Box
2N6395G		500 Units / Box
2N6397G	TO-220AB (Pb-Free)	500 Units / Box
2N6397TG	(1.511.66)	500 Units / Box
2N6399G		500 Units / Box
2N6399TG		500 Units / Box

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
- DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

Mouser Electronics

Authorized Distributor

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Littelfuse:

2N6399G 2N6395G 2N6397TG 2N6394G 2N6397G 2N6394TG 2N6399TG